



UF82N25

Preliminary

Power MOSFET

82A, 250V N-CHANNEL POWER MOSFET

DESCRIPTION

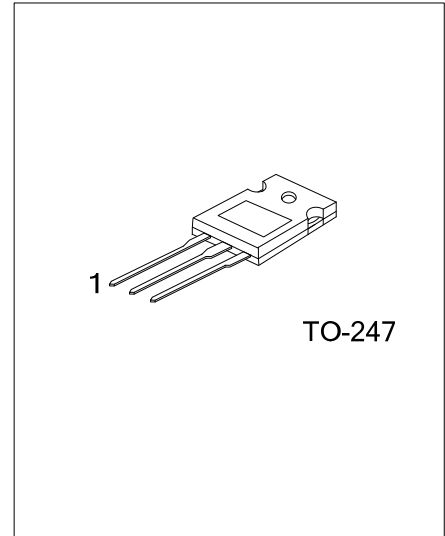
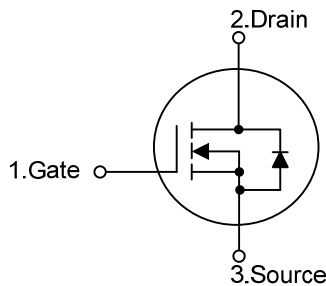
The UTC **UF82N25** is a N-Channel enhancement mode power MOSFET is produced using UTC planar DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength.

FEATURES

* $R_{DS(ON)} \leq 42 \text{ m}\Omega$ @ $V_{GS}=10\text{V}$, $I_D=41\text{A}$

* High Switching Speed

SYMBOL



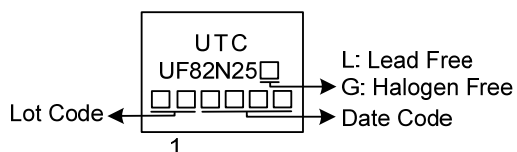
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF82N25L-T47-T	UF82N25G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

UF82N25G-T47-T	(1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube (2) T47: TO-247 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



■ ABSOLUTE MAXIMUM RATINGS (unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DS}	250	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	Continuous	I_D	82
	Pulsed	I_{DM}	164
Single Pulsed Avalanche Energy	E_{AS}	3181	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	6.58	V/ns
Power Dissipation	P_D	360	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 30 \text{ mH}$, $I_{AS} = 14.56\text{A}$, $V_{DD} = 90\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 30\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	40	°C/W
Junction to Case	θ_{JC}	0.347	°C/W

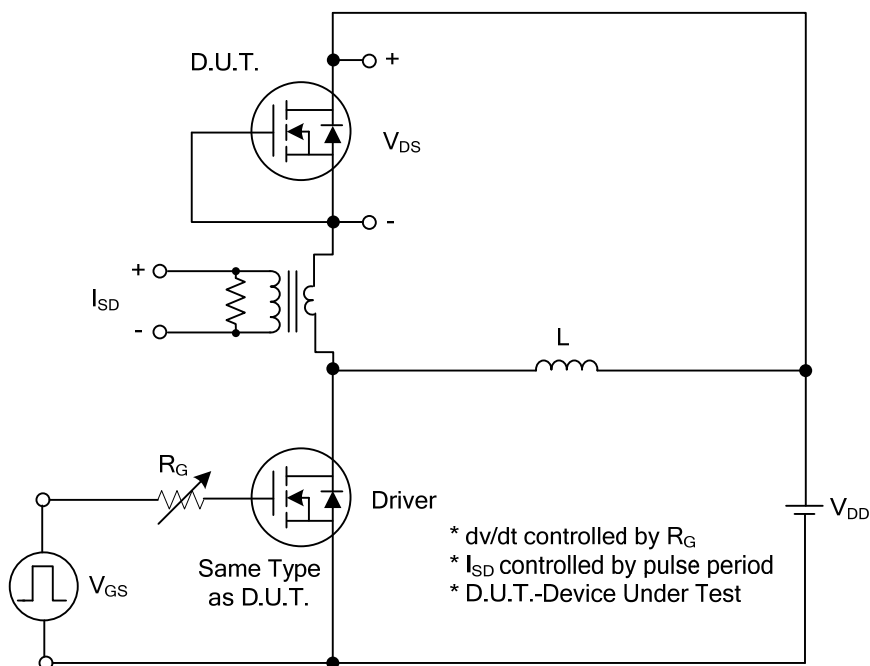
■ ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	250			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =250V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =41A			42	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		5137		pF
Output Capacitance		C _{OSS}			1500		pF
Reverse Transfer Capacitance		C _{RSS}			403		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _{DS} =200V, V _{GS} =10V, I _D =82A (Note 1, 2)		142		nC
Gate to Source Charge		Q _{GS}			38		nC
Gate to Drain Charge		Q _{GD}			65		nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =82A, R _G =25Ω (Note 1, 2)		84		ns
Rise Time		t _R			104		ns
Turn-OFF Delay Time		t _{D(OFF)}			316		ns
Fall-Time		t _F			62		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				82	A
Maximum Body-Diode Pulsed Current		I _{SM}				164	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =82A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time		t _{rr}	I _S =30A, V _{GS} =0V, dI _F /dt=100A/μs		289		ns
Reverse Recovery Charge		Q _{rr}	(Note 1)		3.1		μC

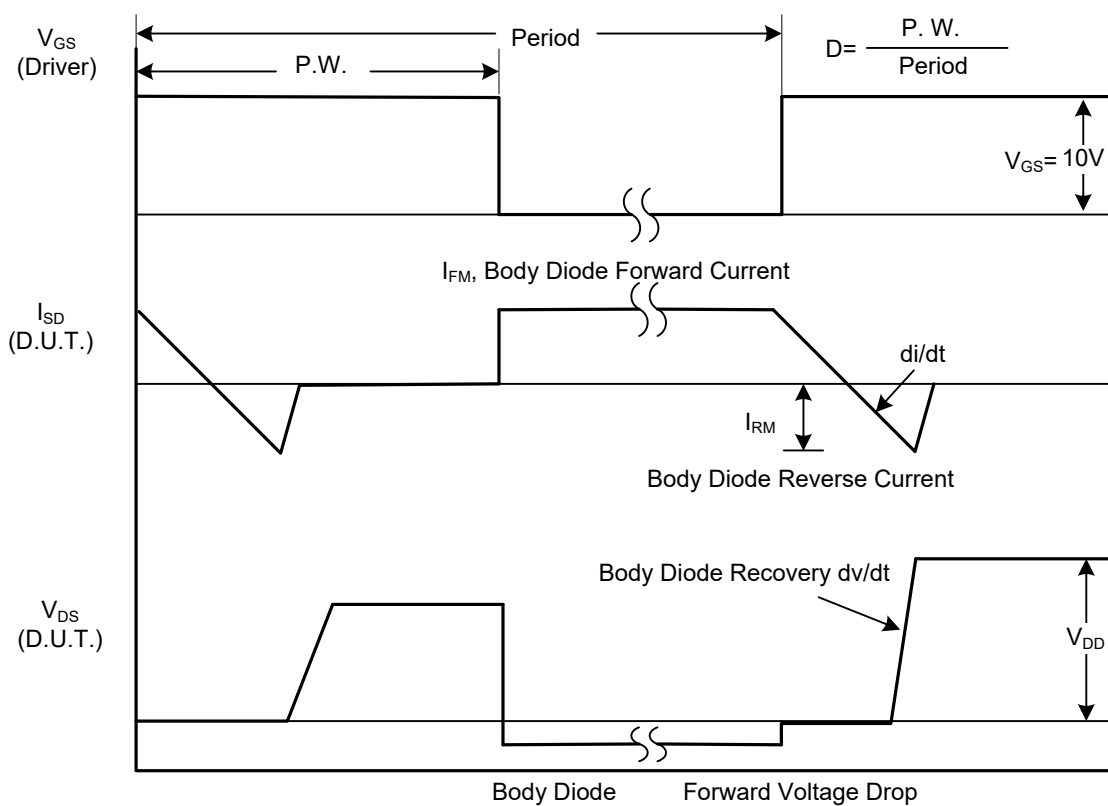
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

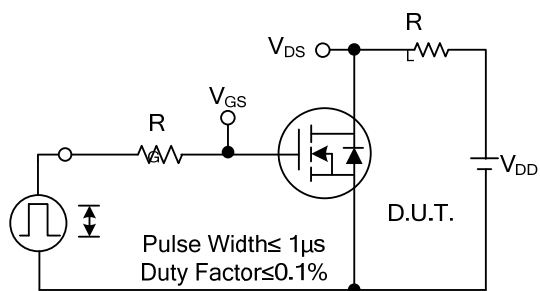


Peak Diode Recovery dv/dt Test Circuit

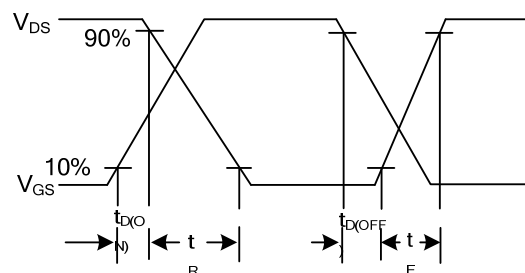


Peak Diode Recovery dv/dt Waveforms

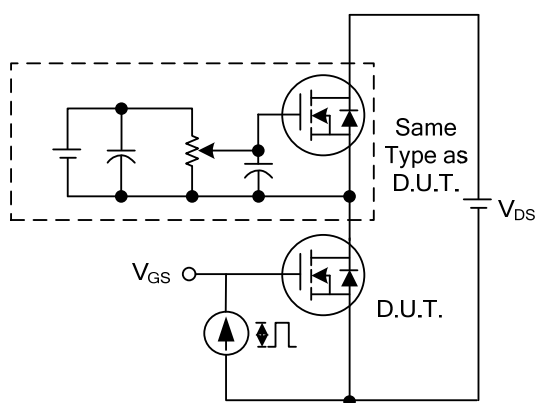
■ TEST CIRCUITS AND WAVEFORMS



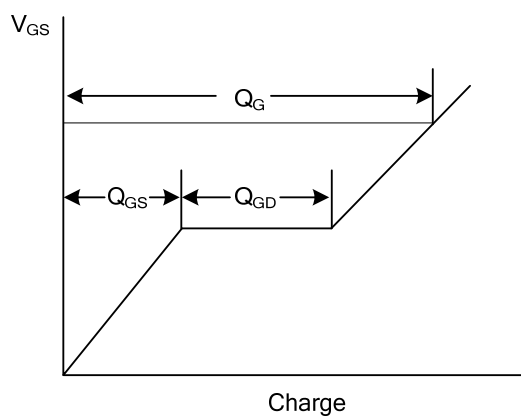
Switching Test Circuit



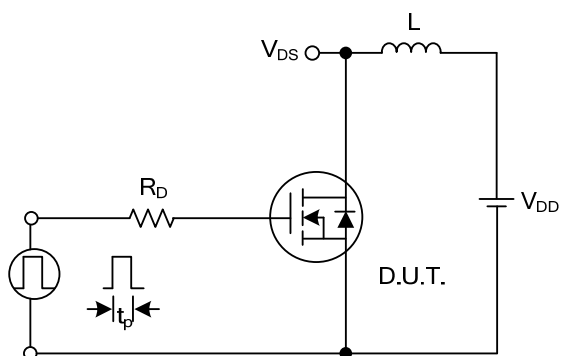
Switching Waveforms



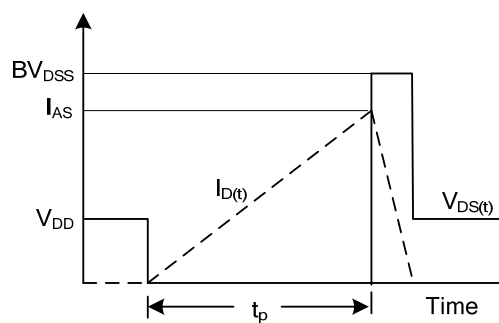
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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